2011 International Meeting for Future of Electron Devices

(IMFEDK 2011)

Suita, Osaka, Japan
19 – 20 May 2011

IEEE Catalog Number: CFP11567-PRT
ISBN: 978-1-61284-145-8

The Conference Theme

"Nanotechnology and Its Impact on Electron Devices"

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H. Inokawa, W Du, M. Kawai, H. Satoh, A. Ono, V. Singh (Shizuoka University)

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([1]NAIST, [2]CREST)

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A. Heya[1], N. Matsuo[1], T. Konaganezawa[2]
([1]University of Hyogo, [2]Japan Synchrotron Radiation Research

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Institute)

14:10-14:30

A-3 **(p.36)** Tight Binding Modeling of Intermediate Band Solar Cells Based on InAs/GaAs Quantum Dot Arrays
A. Mehdipour, M. Ogawa, S. Souma (Kobe University)

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([1]Low-power Electronics Association & Project, [2]Renesas Electronics Corp.)

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T. Kobayashi[1], N. Matsuo[1], A. Heya[1], Y. Omura[2], S. Yokoyama[3]
([1]University of Hyogo, [2]Kansai University, [3]Hiroshima University)

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B-4 **(p.46)** Thin Film Transistors and Photo Diodes Fabricated on Double-Layered Polycrystalline Silicon Films Formed by Green Laser

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K. Yamasaki[1], E. Machida[1], M. Horita[1,2], Y. Ishikawa[1,2], Y. Uraoka[1,2]
([1]NAIST, [2]CREST)

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Special Invited Session

16:40-17:20
T-1 **(p.28)** On-chip Robotics for Biomedical Innovations
F. Arai (Nagoya University)

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Awards & Closing Remark

17:30-17:40	Award Presentation:	Y. Ohmura (Kansai University)
17:40-17:50	Closing Remark:	Y. Ohmura (Kansai University)